



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Taketomi Asami et al. Art Unit : 2815
Serial No. : 10/792,132 Examiner : Joseph H Nguyen
Filed : March 4, 2004
Title : SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE
SAME

MAIL STOP AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Supplemental to the Information Disclosure Statement (IDS) filed March 4, 2004,
Applicants submit the attached corrected form PTO-1449. The corrected form PTO-1449 is
being submitted to add the corresponding page numbers to reference Desig. ID "AKK". The
attached form PTO-1449 includes the corresponding page numbers in bold type.

No fee is believed to be due in connection with this paper. In the event that any fees are
due, please apply any charges or credits to deposit account 06-1050.

Respectfully submitted,

Date: _____

7/12/05

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Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12732-061002	Application No. 10/792,132
Information Disclosure Statement by Applicant (Use several sheets if necessary)		Applicant Taketomi Asami et al.	
		Filing Date March 4, 2004	Group Art Unit

(37 CFR §1.98(b))

U.S. Patent Documents

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA	2001/0014535 A1	08/16/2001	Yamazaki			
	AB	2002/0014625 A1	02/07/2002	Asami et al.			
	AC	2002/0038889 A1	04/04/2002	Yamazaki et al.			
	AD	2002/0043662 A1	04/18/2002	Yamazaki et al.			
	AE	4,987,005	01/22/1991	Suzuki et al.			
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	AAA	6,479,333	11/12/2002	Takano et al.			

Examiner Signature	Date Considered
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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U.S. Patent Documents

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	ABB	6,690,068	02/10/2004	Yamazaki et al.			

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	ACC	11-307783	11/05/1999	JAPAN			ABS	
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	ALL	Seok-Woon Lee et al.; "Low Temperature Poly-Si Thin-Film Transistor Fabrication by Metal-Induced Lateral Crystallization"; IEEE Electron Device Letters, Vol. 17, No. 4; pp. 160-162; April 1996.

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